











Process Flow

Goal

The goal of the project is to microfabricate a [dielectric elastomer actuator](#) (DEA) at the [Toronto Nanofabrication Centre](#). This is the first step in building an artificial muscle fibre prototype.

Steps	Diagram
<ul style="list-style-type: none">Start with a 4" clean silicon wafer.	<p>Base Silicon Wafer</p>  <p>1</p>
<ul style="list-style-type: none">Clean wafer with H₂O₂ + H₂SO₄.Dry with nitrogen gas.Heat on a hotplate to remove moisture.Spin coat AZ4562 photoresist at 4000 rpm for 30 seconds for a 6 µm sacrificial layer.Bake at 100 degrees for 2 minutes.	<p>PR Spin Coating</p>  <p>2</p>
<ul style="list-style-type: none">Deposit metal electrode via e-beam evaporator.2 micrometers of Al, capped with 5 nanometers of Au on both ends to prevent oxidation.Specific machine is the Angstrom Nextdep E-Beam Evaporator.	<p>Al/Au Evaporation</p>  <p>3</p>

<ul style="list-style-type: none"> • Mix Sylgard 186 PDMS monomer and curing agent 10:1 ratio and degas in vacuum desiccator. • Spin coat PDMS at 6000 rpm for 5 minutes for a 4 micrometer film. • Cure in oven at 150 degrees for 15 minutes. 	<h3>PDMS Spin Coating</h3>  <p>4</p>
<ul style="list-style-type: none"> • Put wafer in an O2 plasma chamber for 5 minutes to increase surface roughness. • Specific machine is TePla Technics 100-E Oxygen Plasma Asher. • Repeat step 3 for Al/Au evaporation. 	<h3>Al/Au Evaporation</h3>  <p>5</p>
<ul style="list-style-type: none"> • Repeat step 2 for photoresist spin coating. 	<h3>PR Spin Coating</h3>  <p>6</p>
<ul style="list-style-type: none"> • Pattern the photoresist via photolithography. • Design photomask on L-edit. • Specific machine is the MA6 aligner. • Develop photoresist with AZ 340, in a 1:5 mix with water. 	<h3>PR Patterning</h3>  <p>7</p>

<ul style="list-style-type: none"> • Etch the metal electrodes and PDMS until reaching the bottom photoresist layer. • Wet etch the metal electrodes. • Reactive ion etching with SF6 + O2 chemistry used to etch PDMS. • Specific machine is the Oxford PlasmaPro 100 Cobra ICP-RIE. 	<h3>Reactive Ion Etching</h3>  <p>8</p>
<ul style="list-style-type: none"> • Put wafer in acetone solution and wait for dissolution of photoresist. • Dielectric elastomer actuator will be floating on the surface. 	<h3>PR Dissolution</h3>  <p>9</p>
<ul style="list-style-type: none"> • Fabricate an accompanying Copper plated wafer. Add the cell to the wafer with the bottom electrode in contact. • Place the wafer under the probe station. Connect the input and output to observe compression when charged. 	<h3>Characterization</h3>  <p>10</p>

Notes

- [This article](#) gives a good explanation for how to do the PDMS spin coating.
- To detach PDMS from Wafer use photoresist sacrificial layer. [AZ4562 photoresist](#) is good.
- [This paper](#) gives a good explanation for how to do photolithography + etch of PDMS.
- [This paper](#) deposits gold film on the PDMS via e-beam evaporation.
- [This paper](#) is on increasing surface adhesion of Au film on PDMS through O2 plasma treatment.